

AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph that begins on page 7, line 3 as follows:

After the remainder of the photodiode 14 is produced, it may be doped in a conventional manner as specified by the particular application (step 304). In the embodiments shown in figures 1 and 2, the photodiode 14 is doped in a manner that produces the above noted three regions 20, 22, and 24. Specifically, the photodiode 14 is doped to produce the p-type doped region 20, the n-type doped region 22, and the intrinsic region 24 between the two doped regions. In illustrative embodiments, the p-type doped region 20 is immediately adjacent to the single-crystal silicon base layer 12, while the n-type doped region 22 forms a top diode surface. The p-type doped region 20 illustratively is doped by conventional outdiffusion from the p-type doped single-crystal silicon base. In alternative embodiments, rather than dope the region 22 at this time in the process, it is doped later at 314, i.e., after the topside electrode 16 is formed. Details of this embodiment are discussed below.